TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

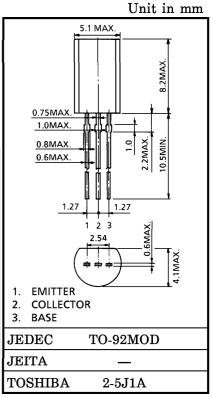
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DRIVER STAGE AMPLIFIER APPLICATIONS VOLTAGE AMPLIFIER APPLICATIONS

- Complementary to 2SC1627A.
- Driver Stage Application of 30 to 35 Watts Amplifiers.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	v_{CBO}	-80	V
Collector-Emitter Voltage	v_{CEO}	-80	V
Emitter-Base Voltage	$v_{ m EBO}$	-5	V
Collector Current	$I_{\mathbb{C}}$	-400	mA
Emitter Current	$\mathbf{I_E}$	400	mA
Collector Power Dissipation	$P_{\mathbf{C}}$	800	mW
Junction Temperature	$\mathrm{T_{j}}$	150	°C
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~150	°C



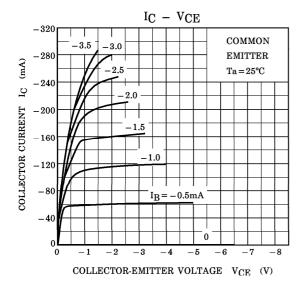
Weight: 0.36g (Typ.)

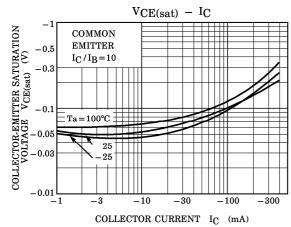
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

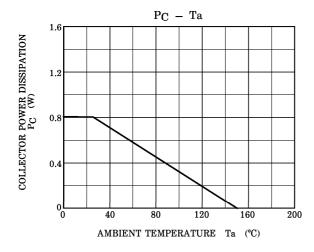
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CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -50V, I_{E} = 0$	_	_	-100	nA
Emitter Cut-off Current	$I_{ m EBO}$	$V_{EB} = -5V, I_C = 0$	_		-100	nA
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	$I_{\rm C} = -5 {\rm mA}, \ I_{\rm B} = 0$	-80	_	_	V
DC Current Gain	hFE(1) (Note)	$V_{CE} = -2V, I_{C} = -50 \text{mA}$	70		240	
	$h_{\mathrm{FE}(2)}$	$V_{CE} = -2V, I_{C} = -200 \text{mA}$	40	1	_	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	$I_C = -200 \text{mA}, I_B = -20 \text{mA}$	_	1	-0.4	V
Base-Emitter Voltage	$ m V_{BE}$	$V_{CE} = -2V$, $I_{C} = -5mA$	-0.55		-0.8	V
Transition Frequency	$ m f_{T}$	$V_{CE} = -10V, I_{C} = -10mA$		100		MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$	_	14		pF

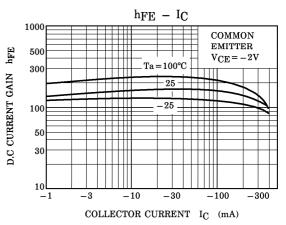
(Note) : $h_{FE(1)}$ Classification O : $70\sim140$, Y : $120\sim240$

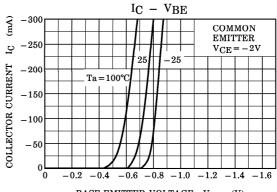
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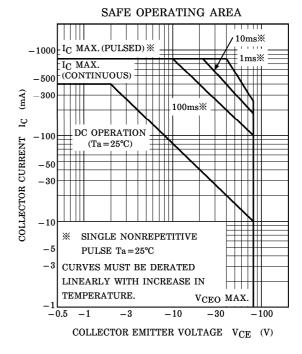








 $BASE\text{-}EMITTER\ VOLTAGE\quad V_{BE}\quad (V)$



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